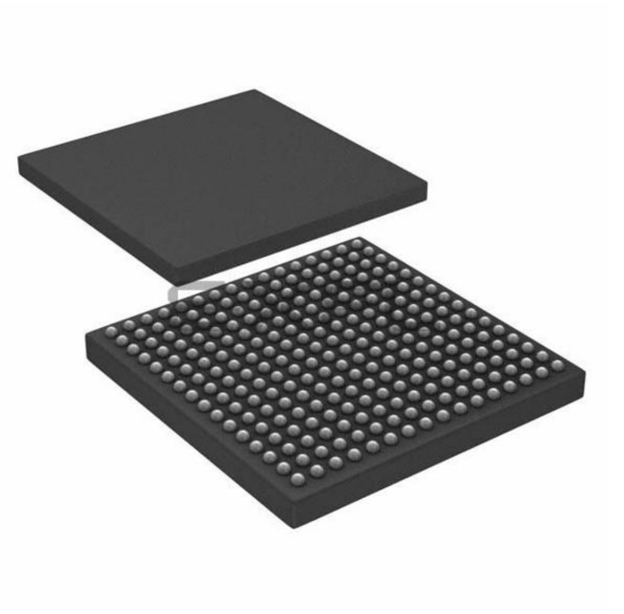

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

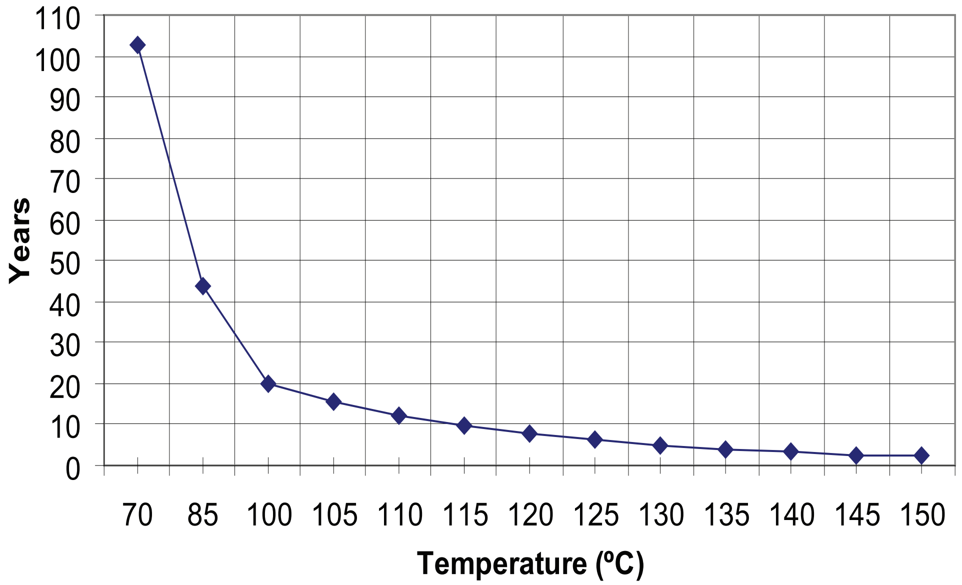
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	147456
Number of I/O	177
Number of Gates	1000000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p1000-1fg256i

Tj (°C)	HTR Lifetime (yrs)
70	102.7
85	43.8
100	20.0
105	15.6
110	12.3
115	9.7
120	7.7
125	6.2
130	5.0
135	4.0
140	3.3
145	2.7
150	2.2



Note: *HTR time is the period during which you would not expect a verify failure due to flash cell leakage.*

Figure 2-1 • **High-Temperature Data Retention (HTR)**

Table 2-3 • **Flash Programming Limits – Retention, Storage and Operating Temperature**[1]

Product Grade	**Programming Cycles**	**Program Retention (biased/unbiased)**	**Maximum Storage Temperature T_{STG} (°C)**	**Maximum Operating Junction Temperature T_J (°C)**[2]
Commercial	500	20 years	110	100
Industrial	500	20 years	110	100

1. *This is a stress rating only; functional operation at any condition other than those indicated is not implied.*
2. *These limits apply for program/data retention only. Refer to Table 2-1 on page 2-1 and Table 2-2 for device operating conditions and absolute limits.*

Table 2-4 • **Overshoot and Undershoot Limits** [1]

VCCI and VMV	**Average VCCI–GND Overshoot or Undershoot Duration as a Percentage of Clock Cycle**[2]	**Maximum Overshoot/ Undershoot**[2]
2.7 V or less	10%	1.4 V
	5%	1.49 V
3 V	10%	1.1 V
	5%	1.19 V
3.3 V	10%	0.79 V
	5%	0.88 V
3.6 V	10%	0.45 V
	5%	0.54 V

Notes:

1. *Based on reliability requirements at 85°C.*
2. *The duration is allowed at one out of six clock cycles. If the overshoot/undershoot occurs at one out of two cycles, the maximum overshoot/undershoot has to be reduced by 0.15 V.*
3. *This table does not provide PCI overshoot/undershoot limits.*

I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every ProASIC®3 device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges.

In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in Figure 2-2 on page 2-5.

There are five regions to consider during power-up.

ProASIC3 I/Os are activated only if ALL of the following three conditions are met:

1. VCC and VCCI are above the minimum specified trip points (Figure 2-2 on page 2-5).
2. VCCI > VCC – 0.75 V (typical)
3. Chip is in the operating mode.

VCCI Trip Point:
Ramping up: 0.6 V < trip_point_up < 1.2 V
Ramping down: 0.5 V < trip_point_down < 1.1 V

VCC Trip Point:
Ramping up: 0.6 V < trip_point_up < 1.1 V
Ramping down: 0.5 V < trip_point_down < 1 V

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.
- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper power-up behavior. Power ramp-up should be monotonic at least until VCC and VCCPLLX exceed brownout activation levels. The VCC activation level is specified as 1.1 V worst-case (see Figure 2-2 on page 2-5 for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels (0.75 V ± 0.25 V), the PLL output lock signal goes low and/or the output clock is lost. Refer to the "Power-Up/Down Behavior of Low Power Flash Devices" chapter of the *ProASIC3 FPGA Fabric User's Guide* for information on clock and lock recovery.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers

Output buffers, after 200 ns delay from input buffer activation.

Thermal Characteristics

Introduction

The temperature variable in the Microsemi Designer software refers to the junction temperature, not the ambient temperature. This is an important distinction because dynamic and static power consumption cause the chip junction to be higher than the ambient temperature.

EQ can be used to calculate junction temperature.

$$T_J = \text{Junction Temperature} = \Delta T + T_A$$

where:

T_A = Ambient Temperature

ΔT = Temperature gradient between junction (silicon) and ambient $\Delta T = \theta_{ja} * P$

θ_{ja} = Junction-to-ambient of the package. θ_{ja} numbers are located in Table 2-5 on page 2-6.

P = Power dissipation

Single-Ended I/O Characteristics

3.3 V LVTTL / 3.3 V LVCMOS

Low-Voltage Transistor–Transistor Logic (LVTTL) is a general-purpose standard (EIA/JESD) for 3.3 V applications. It uses an LVTTL input buffer and push-pull output buffer.

Table 2-37 • **Minimum and Maximum DC Input and Output Levels Applicable to Advanced I/O Banks**

3.3 V LVTTL / 3.3 V LVCMOS	**VIL**		**VIH**		**VOL**	**VOH**	**IOL**	**IOH**	**IOSL**	**IOSH**	**IIL**[1]	**IIH**[2]
Drive Strength	**Min V**	**Max V**	**Min V**	**Max V**	**Max V**	**Min V**	**mA**	**mA**	**Max mA**[3]	**Max mA**[3]	**µA**[4]	**µA**[4]
2 mA	–0.3	0.8	2	3.6	0.4	2.4	2	2	27	25	10	10
4 mA	–0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	10	10
6 mA	–0.3	0.8	2	3.6	0.4	2.4	6	6	54	51	10	10
8 mA	–0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	10	10
12 mA	–0.3	0.8	2	3.6	0.4	2.4	12	12	109	103	10	10
16 mA	–0.3	0.8	2	3.6	0.4	2.4	16	16	127	132	10	10
24 mA	–0.3	0.8	2	3.6	0.4	2.4	24	24	181	268	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

Table 2-38 • **Minimum and Maximum DC Input and Output Levels Applicable to Standard Plus I/O Banks**

3.3 V LVTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	**IOL**	**IOH**	**IOSL**	**IOSH**	**IIL**[1]	**IIH**[2]
Drive Strength	**Min V**	**Max V**	**Min V**	**Max V**	**Max V**	**Min V**	**mA**	**mA**	**Max mA**[3]	**Max mA**[3]	**µA**[4]	**µA**[4]
2 mA	–0.3	0.8	2	3.6	0.4	2.4	2	2	27	25	10	10
4 mA	–0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	10	10
6 mA	–0.3	0.8	2	3.6	0.4	2.4	6	6	54	51	10	10
8 mA	–0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	10	10
12 mA	–0.3	0.8	2	3.6	0.4	2.4	12	12	109	103	10	10
16 mA	–0.3	0.8	2	3.6	0.4	2.4	16	16	109	103	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

Timing Characteristics

***Table 2-41* • 3.3 V LVTTL / 3.3 V LVCMOS High Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	7.66	0.04	1.02	0.43	7.80	6.59	2.65	2.61	10.03	8.82	ns
	–1	0.56	6.51	0.04	0.86	0.36	6.63	5.60	2.25	2.22	8.54	7.51	ns
	–2	0.49	5.72	0.03	0.76	0.32	5.82	4.92	1.98	1.95	7.49	6.59	ns
4 mA	Std.	0.66	7.66	0.04	1.02	0.43	7.80	6.59	2.65	2.61	10.03	8.82	ns
	–1	0.56	6.51	0.04	0.86	0.36	6.63	5.60	2.25	2.22	8.54	7.51	ns
	–2	0.49	5.72	0.03	0.76	0.32	5.82	4.92	1.98	1.95	7.49	6.59	ns
6 mA	Std.	0.66	4.91	0.04	1.02	0.43	5.00	4.07	2.99	3.20	7.23	6.31	ns
	–1	0.56	4.17	0.04	0.86	0.36	4.25	3.46	2.54	2.73	6.15	5.36	ns
	–2	0.49	3.66	0.03	0.76	0.32	3.73	3.04	2.23	2.39	5.40	4.71	ns
8 mA	Std.	0.66	4.91	0.04	1.02	0.43	5.00	4.07	2.99	3.20	7.23	6.31	ns
	–1	0.56	4.17	0.04	0.86	0.36	4.25	3.46	2.54	2.73	6.15	5.36	ns
	–2	0.49	3.66	0.03	0.76	0.32	3.73	3.04	2.23	2.39	5.40	4.71	ns
12 mA	Std.	0.66	3.53	0.04	1.02	0.43	3.60	2.82	3.21	3.58	5.83	5.06	ns
	–1	0.56	3.00	0.04	0.86	0.36	3.06	2.40	2.73	3.05	4.96	4.30	ns
	–2	0.49	2.64	0.03	0.76	0.32	2.69	2.11	2.40	2.68	4.36	3.78	ns
16 mA	Std.	0.66	3.33	0.04	1.02	0.43	3.39	2.56	3.26	3.68	5.63	4.80	ns
	–1	0.56	2.83	0.04	0.86	0.36	2.89	2.18	2.77	3.13	4.79	4.08	ns
	–2	0.49	2.49	0.03	0.76	0.32	2.53	1.91	2.44	2.75	4.20	3.58	ns
24 mA	Std.	0.66	3.08	0.04	1.02	0.43	3.13	2.12	3.32	4.06	5.37	4.35	ns
	–1	0.56	2.62	0.04	0.86	0.36	2.66	1.80	2.83	3.45	4.57	3.70	ns
	–2	0.49	2.30	0.03	0.76	0.32	2.34	1.58	2.48	3.03	4.01	3.25	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Timing Characteristics

Table 2-50 • **3.3 V LVTTL / 3.3 V LVCMOS High Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Advanced I/O Banks

Drive Strength	Equiv. Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	4 mA	Std.	0.60	11.84	0.04	1.02	0.43	11.84	10.00	4.10	4.04	15.23	13.40	ns
		–1	0.51	10.07	0.04	0.86	0.36	10.07	8.51	3.48	3.44	12.96	11.40	ns
		–2	0.45	8.84	0.03	0.76	0.32	8.84	7.47	3.06	3.02	11.38	10.00	ns
100 µA	6 mA	Std.	0.60	7.59	0.04	1.02	0.43	7.59	6.18	4.62	4.95	10.98	9.57	ns
		–1	0.51	6.45	0.04	0.86	0.36	6.45	5.25	3.93	4.21	9.34	8.14	ns
		–2	0.45	5.67	0.03	0.76	0.32	5.67	4.61	3.45	3.70	8.20	7.15	ns
100 µA	8 mA	Std.	0.60	7.59	0.04	1.02	0.43	7.59	6.18	4.62	4.95	10.98	9.57	ns
		–1	0.51	6.45	0.04	0.86	0.36	6.45	5.25	3.93	4.21	9.34	8.14	ns
		–2	0.45	5.67	0.03	0.76	0.32	5.67	4.61	3.45	3.70	8.20	7.15	ns
100 µA	12 mA	Std.	0.60	5.46	0.04	1.02	0.43	5.46	4.29	4.97	5.54	8.86	7.68	ns
		–1	0.51	4.65	0.04	0.86	0.36	4.65	3.65	4.22	4.71	7.53	6.54	ns
		–2	0.45	4.08	0.03	0.76	0.32	4.08	3.20	3.71	4.14	6.61	5.74	ns
100 µA	16 mA	Std.	0.60	5.15	0.04	1.02	0.43	5.15	3.89	5.04	5.69	8.55	7.29	ns
		–1	0.51	4.38	0.04	0.86	0.36	4.38	3.31	4.29	4.84	7.27	6.20	ns
		–2	0.45	3.85	0.03	0.76	0.32	3.85	2.91	3.77	4.25	6.38	5.44	ns
100 µA	24 mA	Std.	0.60	4.75	0.04	1.02	0.43	4.75	3.22	5.14	6.28	8.15	6.61	ns
		–1	0.51	4.04	0.04	0.86	0.36	4.04	2.74	4.37	5.34	6.93	5.62	ns
		–2	0.45	3.55	0.03	0.76	0.32	3.55	2.40	3.84	4.69	6.09	4.94	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *Software default selection highlighted in gray.*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-52 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus I/O Banks

Drive Strength	Equiv. Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	2 mA	Std.	0.60	11.14	0.04	1.52	0.43	11.14	9.54	3.51	3.61	14.53	12.94	ns
		–1	0.51	9.48	0.04	1.29	0.36	9.48	8.12	2.99	3.07	12.36	11.00	ns
		–2	0.45	8.32	0.03	1.14	0.32	8.32	7.13	2.62	2.70	10.85	9.66	ns
100 µA	4 mA	Std.	0.60	6.96	0.04	1.52	0.43	6.96	5.79	3.99	4.45	10.35	9.19	ns
		–1	0.51	5.92	0.04	1.29	0.36	5.92	4.93	3.39	3.78	8.81	7.82	ns
		–2	0.45	5.20	0.03	1.14	0.32	5.20	4.33	2.98	3.32	7.73	6.86	ns
100 µA	6 mA	Std.	0.60	6.96	0.04	1.52	0.43	6.96	5.79	3.99	4.45	10.35	9.19	ns
		–1	0.51	5.92	0.04	1.29	0.36	5.92	4.93	3.39	3.78	8.81	7.82	ns
		–2	0.45	5.20	0.03	1.14	0.32	5.20	4.33	2.98	3.32	7.73	6.86	ns
100 µA	8 mA	Std.	0.60	4.89	0.04	1.52	0.43	4.89	3.92	4.31	4.98	8.28	7.32	ns
		–1	0.51	4.16	0.04	1.29	0.36	4.16	3.34	3.67	4.24	7.04	6.22	ns
		–2	0.45	3.65	0.03	1.14	0.32	3.65	2.93	3.22	3.72	6.18	5.46	ns
100 µA	16 mA	Std.	0.60	4.89	0.04	1.52	0.43	4.89	3.92	4.31	4.98	8.28	7.32	ns
		–1	0.51	4.16	0.04	1.29	0.36	4.16	3.34	3.67	4.24	7.04	6.22	ns
		–2	0.45	3.65	0.03	1.14	0.32	3.65	2.93	3.22	3.72	6.18	5.46	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *Software default selection highlighted in gray.*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-54 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew
Commercial-Case Conditions: TJ = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard I/O Banks

Drive Strength	Equiv. Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	2 mA	Std.	0.60	10.93	0.04	1.52	0.43	10.93	9.46	3.20	3.32	ns
		–1	0.51	9.29	0.04	1.29	0.36	9.29	8.04	2.72	2.82	ns
		–2	0.45	8.16	0.03	1.13	0.32	8.16	7.06	2.39	2.48	ns
100 µA	4 mA	Std.	0.60	10.93	0.04	1.52	0.43	10.93	9.46	3.20	3.32	ns
		–1	0.51	9.29	0.04	1.29	0.36	9.29	8.04	2.72	2.82	ns
		–2	0.45	8.16	0.03	1.13	0.32	8.16	7.06	2.39	2.48	ns
100 µA	6 mA	Std.	0.60	6.82	0.04	1.52	0.43	6.82	5.70	3.70	4.16	ns
		–1	0.51	5.80	0.04	1.29	0.36	5.80	4.85	3.15	3.54	ns
		–2	0.45	5.09	0.03	1.13	0.32	5.09	4.25	2.77	3.11	ns
100 µA	8 mA	Std.	0.60	6.82	0.04	1.52	0.43	6.82	5.70	3.70	4.16	ns
		–1	0.51	5.80	0.04	1.29	0.36	5.80	4.85	3.15	3.54	ns
		–2	0.45	5.09	0.03	1.13	0.32	5.09	4.25	2.77	3.11	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *Software default selection highlighted in gray.*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-68 • **Minimum and Maximum DC Input and Output Levels Applicable to Standard I/O Banks**

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	**Min. V**	**Max. V**	**Min. V**	**Max. V**	**Max. V**	**Min. V**	**mA**	**mA**	**Max. mA[3]**	**Max. mA[3]**	**μA[4]**	**μA[4]**
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	2	2	9	11	10	10
4 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	4	4	17	22	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

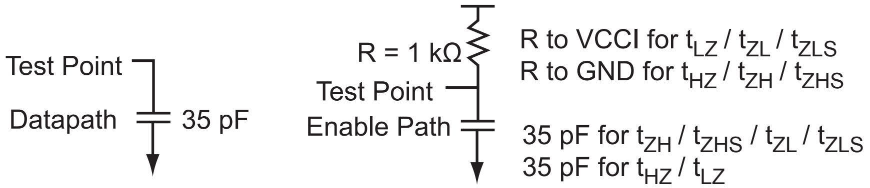


Figure 2-9 • **AC Loading**

Table 2-69 • **AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	1.8	0.9	35

Note: *Measuring point = Vtrip. See Table 2-22 on page 2-22 for a complete table of trip points.

***Table 2-81* • 1.5 V LVCMOS Low Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	12.78	0.04	1.44	0.43	12.81	12.78	3.40	2.64	15.05	15.02	ns
	–1	0.56	10.87	0.04	1.22	0.36	10.90	10.87	2.89	2.25	12.80	12.78	ns
	–2	0.49	9.55	0.03	1.07	0.32	9.57	9.55	2.54	1.97	11.24	11.22	ns
4 mA	Std.	0.66	10.01	0.04	1.44	0.43	10.19	9.55	3.75	3.27	12.43	11.78	ns
	–1	0.56	8.51	0.04	1.22	0.36	8.67	8.12	3.19	2.78	10.57	10.02	ns
	–2	0.49	7.47	0.03	1.07	0.32	7.61	7.13	2.80	2.44	9.28	8.80	ns
6 mA	Std.	0.66	9.33	0.04	1.44	0.43	9.51	8.89	3.83	3.43	11.74	11.13	ns
	–1	0.56	7.94	0.04	1.22	0.36	8.09	7.56	3.26	2.92	9.99	9.47	ns
	–2	0.49	6.97	0.03	1.07	0.32	7.10	6.64	2.86	2.56	8.77	8.31	ns
8 mA	Std.	0.66	8.91	0.04	1.44	0.43	9.07	8.89	3.95	4.05	11.31	11.13	ns
	–1	0.56	7.58	0.04	1.22	0.36	7.72	7.57	3.36	3.44	9.62	9.47	ns
	–2	0.49	6.65	0.03	1.07	0.32	6.78	6.64	2.95	3.02	8.45	8.31	ns
12 mA	Std.	0.66	8.91	0.04	1.44	0.43	9.07	8.89	3.95	4.05	11.31	11.13	ns
	–1	0.56	7.58	0.04	1.22	0.36	7.72	7.57	3.36	3.44	9.62	9.47	ns
	–2	0.49	6.65	0.03	1.07	0.32	6.78	6.64	2.95	3.02	8.45	8.31	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

***Table 2-82* • 1.5 V LVCMOS High Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	7.83	0.04	1.42	0.43	6.42	7.83	2.71	2.55	8.65	10.07	ns
	–1	0.56	6.66	0.04	1.21	0.36	5.46	6.66	2.31	2.17	7.36	8.56	ns
	–2	0.49	5.85	0.03	1.06	0.32	4.79	5.85	2.02	1.90	6.46	7.52	ns
4 mA	Std.	0.66	4.84	0.04	1.42	0.43	4.49	4.84	3.03	3.13	6.72	7.08	ns
	–1	0.56	4.12	0.04	1.21	0.36	3.82	4.12	2.58	2.66	5.72	6.02	ns
	–2	0.49	3.61	0.03	1.06	0.32	3.35	3.61	2.26	2.34	5.02	5.28	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

***Table 2-121* • A3P250 FIFO 1k×4**
Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{ENS}	REN, WEN Setup Time	4.05	4.61	5.42	ns
t_{ENH}	REN, WEN Hold Time	0.00	0.00	0.00	ns
t_{BKS}	BLK Setup Time	0.19	0.22	0.26	ns
t_{BKH}	BLK Hold Time	0.00	0.00	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.18	0.21	0.25	ns
t_{DH}	Input Data (WD) Hold Time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	2.36	2.68	3.15	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	0.89	1.02	1.20	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	1.72	1.96	2.30	ns
t_{WCKFF}	WCLK High to Full Flag Valid	1.63	1.86	2.18	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	6.19	7.05	8.29	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	1.69	1.93	2.27	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	6.13	6.98	8.20	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on RD (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET Removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET Recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.21	0.24	0.29	ns
t_{CYC}	Clock Cycle Time	3.23	3.68	4.32	ns
F_{MAX}	Maximum Frequency for FIFO	310	272	231	MHz

QN132	
Pin Number	**A3P030 Function**
C17	IO51RSB1
C18	NC
C19	TCK
C20	NC
C21	VPUMP
C22	VJTAG
C23	NC
C24	NC
C25	NC
C26	GDB0/IO38RSB0
C27	NC
C28	VCCIB0
C29	IO32RSB0
C30	IO29RSB0
C31	IO28RSB0
C32	IO25RSB0
C33	NC
C34	NC
C35	VCCIB0
C36	IO17RSB0
C37	IO14RSB0
C38	IO11RSB0
C39	IO07RSB0
C40	IO04RSB0
D1	GND
D2	GND
D3	GND
D4	GND

PQ208 – Top View

Note

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

PQ208	
Pin Number	**A3P250 Function**
1	GND
2	GAA2/IO118UDB3
3	IO118VDB3
4	GAB2/IO117UDB3
5	IO117VDB3
6	GAC2/IO116UDB3
7	IO116VDB3
8	IO115UDB3
9	IO115VDB3
10	IO114UDB3
11	IO114VDB3
12	IO113PDB3
13	IO113NDB3
14	IO112PDB3
15	IO112NDB3
16	VCC
17	GND
18	VCCIB3
19	IO111PDB3
20	IO111NDB3
21	GFC1/IO110PDB3
22	GFC0/IO110NDB3
23	GFB1/IO109PDB3
24	GFB0/IO109NDB3
25	VCOMPLF
26	GFA0/IO108NPB3
27	VCCPLF
28	GFA1/IO108PPB3
29	GND
30	GFA2/IO107PDB3
31	IO107NDB3
32	GFB2/IO106PDB3
33	IO106NDB3
34	GFC2/IO105PDB3
35	IO105NDB3
36	NC
37	IO104PDB3
38	IO104NDB3
39	IO103PSB3
40	VCCIB3
41	GND
42	IO101PDB3
43	IO101NDB3
44	GEC1/IO100PDB3
45	GEC0/IO100NDB3
46	GEB1/IO99PDB3
47	GEB0/IO99NDB3
48	GEA1/IO98PDB3
49	GEA0/IO98NDB3
50	VMV3
51	GNDQ
52	GND
53	NC
54	NC
55	GEA2/IO97RSB2
56	GEB2/IO96RSB2
57	GEC2/IO95RSB2
58	IO94RSB2
59	IO93RSB2
60	IO92RSB2
61	IO91RSB2
62	VCCIB2
63	IO90RSB2
64	IO89RSB2
65	GND
66	IO88RSB2
67	IO87RSB2
68	IO86RSB2
69	IO85RSB2
70	IO84RSB2
71	VCC
72	VCCIB2
73	IO83RSB2
74	IO82RSB2
75	IO81RSB2
76	IO80RSB2
77	IO79RSB2
78	IO78RSB2
79	IO77RSB2
80	IO76RSB2
81	GND
82	IO75RSB2
83	IO74RSB2
84	IO73RSB2
85	IO72RSB2
86	IO71RSB2
87	IO70RSB2
88	VCC
89	VCCIB2
90	IO69RSB2
91	IO68RSB2
92	IO67RSB2
93	IO66RSB2
94	IO65RSB2
95	IO64RSB2
96	GDC2/IO63RSB2
97	GND
98	GDB2/IO62RSB2
99	GDA2/IO61RSB2
100	GNDQ
101	TCK
102	TDI
103	TMS
104	VMV2
105	GND
106	VPUMP
107	NC
108	TDO

FG144	
Pin Number	**A3P250 Function**
K1	GEB0/IO99NDB3
K2	GEA1/IO98PDB3
K3	GEA0/IO98NDB3
K4	GEA2/IO97RSB2
K5	IO90RSB2
K6	IO84RSB2
K7	GND
K8	IO66RSB2
K9	GDC2/IO63RSB2
K10	GND
K11	GDA0/IO60VDB1
K12	GDB0/IO59VDB1
L1	GND
L2	VMV3
L3	GEB2/IO96RSB2
L4	IO91RSB2
L5	VCCIB2
L6	IO82RSB2
L7	IO80RSB2
L8	IO72RSB2
L9	TMS
L10	VJTAG
L11	VMV2
L12	TRST
M1	GNDQ
M2	GEC2/IO95RSB2
M3	IO92RSB2
M4	IO89RSB2
M5	IO87RSB2
M6	IO85RSB2
M7	IO78RSB2
M8	IO76RSB2
M9	TDI
M10	VCCIB2
M11	VPUMP
M12	GNDQ

FG144	
Pin Number	**A3P600 Function**
K1	GEB0/IO145NDB3
K2	GEA1/IO144PDB3
K3	GEA0/IO144NDB3
K4	GEA2/IO143RSB2
K5	IO119RSB2
K6	IO111RSB2
K7	GND
K8	IO94RSB2
K9	GDC2/IO91RSB2
K10	GND
K11	GDA0/IO88NDB1
K12	GDB0/IO87NDB1
L1	GND
L2	VMV3
L3	GEB2/IO142RSB2
L4	IO136RSB2
L5	VCCIB2
L6	IO115RSB2
L7	IO103RSB2
L8	IO97RSB2
L9	TMS
L10	VJTAG
L11	VMV2
L12	TRST
M1	GNDQ
M2	GEC2/IO141RSB2
M3	IO138RSB2
M4	IO123RSB2
M5	IO126RSB2
M6	IO134RSB2
M7	IO108RSB2
M8	IO99RSB2
M9	TDI
M10	VCCIB2
M11	VPUMP
M12	GNDQ

FG144	
Pin Number	**A3P1000 Function**
K1	GEB0/IO189NDB3
K2	GEA1/IO188PDB3
K3	GEA0/IO188NDB3
K4	GEA2/IO187RSB2
K5	IO169RSB2
K6	IO152RSB2
K7	GND
K8	IO117RSB2
K9	GDC2/IO116RSB2
K10	GND
K11	GDA0/IO113NDB1
K12	GDB0/IO112NDB1
L1	GND
L2	VMV3
L3	GEB2/IO186RSB2
L4	IO172RSB2
L5	VCCIB2
L6	IO153RSB2
L7	IO144RSB2
L8	IO140RSB2
L9	TMS
L10	VJTAG
L11	VMV2
L12	TRST
M1	GNDQ
M2	GEC2/IO185RSB2
M3	IO173RSB2
M4	IO168RSB2
M5	IO161RSB2
M6	IO156RSB2
M7	IO145RSB2
M8	IO141RSB2
M9	TDI
M10	VCCIB2
M11	VPUMP
M12	GNDQ

FG256	
Pin Number	**A3P400 Function**
A1	GND
A2	GAA0/IO00RSB0
A3	GAA1/IO01RSB0
A4	GAB0/IO02RSB0
A5	IO16RSB0
A6	IO17RSB0
A7	IO22RSB0
A8	IO28RSB0
A9	IO34RSB0
A10	IO37RSB0
A11	IO41RSB0
A12	IO43RSB0
A13	GBB1/IO57RSB0
A14	GBA0/IO58RSB0
A15	GBA1/IO59RSB0
A16	GND
B1	GAB2/IO154UDB3
B2	GAA2/IO155UDB3
B3	IO12RSB0
B4	GAB1/IO03RSB0
B5	IO13RSB0
B6	IO14RSB0
B7	IO21RSB0
B8	IO27RSB0
B9	IO32RSB0
B10	IO38RSB0
B11	IO42RSB0
B12	GBC1/IO55RSB0
B13	GBB0/IO56RSB0
B14	IO44RSB0
B15	GBA2/IO60PDB1
B16	IO60NDB1
C1	IO154VDB3
C2	IO155VDB3
C3	IO11RSB0
C4	IO07RSB0
C5	GAC0/IO04RSB0
C6	GAC1/IO05RSB0
C7	IO20RSB0
C8	IO24RSB0
C9	IO33RSB0
C10	IO39RSB0
C11	IO45RSB0
C12	GBC0/IO54RSB0
C13	IO48RSB0
C14	VMV0
C15	IO61NPB1
C16	IO63PDB1
D1	IO151VDB3
D2	IO151UDB3
D3	GAC2/IO153UDB3
D4	IO06RSB0
D5	GNDQ
D6	IO10RSB0
D7	IO19RSB0
D8	IO26RSB0
D9	IO30RSB0
D10	IO40RSB0
D11	IO46RSB0
D12	GNDQ
D13	IO47RSB0
D14	GBB2/IO61PPB1
D15	IO53RSB0
D16	IO63NDB1
E1	IO150PDB3
E2	IO08RSB0
E3	IO153VDB3
E4	IO152VDB3
E5	VMV0
E6	VCCIB0
E7	VCCIB0
E8	IO25RSB0
E9	IO31RSB0
E10	VCCIB0
E11	VCCIB0
E12	VMV1
E13	GBC2/IO62PDB1
E14	IO65RSB1
E15	IO52RSB0
E16	IO66PDB1
F1	IO150NDB3
F2	IO149NPB3
F3	IO09RSB0
F4	IO152UDB3
F5	VCCIB3
F6	GND
F7	VCC
F8	VCC
F9	VCC
F10	VCC
F11	GND
F12	VCCIB1
F13	IO62NDB1
F14	IO49RSB0
F15	IO64PPB1
F16	IO66NDB1
G1	IO148NDB3
G2	IO148PDB3
G3	IO149PPB3
G4	GFC1/IO147PPB3
G5	VCCIB3
G6	VCC
G7	GND
G8	GND
G9	GND
G10	GND
G11	VCC
G12	VCCIB1

FG484	
Pin Number	**A3P600 Function**
Y15	VCC
Y16	NC
Y17	NC
Y18	GND
Y19	NC
Y20	NC
Y21	NC
Y22	VCCIB1
AA1	GND
AA2	VCCIB3
AA3	NC
AA4	NC
AA5	NC
AA6	IO135RSB2
AA7	IO133RSB2
AA8	NC
AA9	NC
AA10	NC
AA11	NC
AA12	NC
AA13	NC
AA14	NC
AA15	NC
AA16	IO101RSB2
AA17	NC
AA18	NC
AA19	NC
AA20	NC
AA21	VCCIB1
AA22	GND
AB1	GND
AB2	GND
AB3	VCCIB2
AB4	NC
AB5	NC
AB6	IO130RSB2

FG484	
Pin Number	**A3P600 Function**
AB7	IO128RSB2
AB8	IO122RSB2
AB9	IO116RSB2
AB10	NC
AB11	NC
AB12	IO113RSB2
AB13	IO112RSB2
AB14	NC
AB15	NC
AB16	IO100RSB2
AB17	IO95RSB2
AB18	NC
AB19	NC
AB20	VCCIB2
AB21	GND
AB22	GND

FG484	
Pin Number	**A3P1000 Function**
E21	NC
E22	IO84PDB1
F1	NC
F2	IO215PDB3
F3	IO215NDB3
F4	IO224NDB3
F5	IO225NDB3
F6	VMV3
F7	IO11RSB0
F8	GAC0/IO04RSB0
F9	GAC1/IO05RSB0
F10	IO25RSB0
F11	IO36RSB0
F12	IO42RSB0
F13	IO49RSB0
F14	IO56RSB0
F15	GBC0/IO72RSB0
F16	IO62RSB0
F17	VMV0
F18	IO78NDB1
F19	IO81NDB1
F20	IO82PPB1
F21	NC
F22	IO84NDB1
G1	IO214NDB3
G2	IO214PDB3
G3	NC
G4	IO222NDB3
G5	IO222PDB3
G6	GAC2/IO223PDB3
G7	IO223NDB3
G8	GNDQ
G9	IO23RSB0
G10	IO29RSB0
G11	IO33RSB0
G12	IO46RSB0
G13	IO52RSB0
G14	IO60RSB0
G15	GNDQ
G16	IO80NDB1
G17	GBB2/IO79PDB1
G18	IO79NDB1
G19	IO82NPB1
G20	IO85PDB1
G21	IO85NDB1
G22	NC
H1	NC
H2	NC
H3	VCC
H4	IO217PDB3
H5	IO218PDB3
H6	IO221NDB3
H7	IO221PDB3
H8	VMV0
H9	VCCIB0
H10	VCCIB0
H11	IO38RSB0
H12	IO47RSB0
H13	VCCIB0
H14	VCCIB0
H15	VMV1
H16	GBC2/IO80PDB1
H17	IO83PPB1
H18	IO86PPB1
H19	IO87PDB1
H20	VCC
H21	NC
H22	NC
J1	IO212NDB3
J2	IO212PDB3
J3	NC
J4	IO217NDB3
J5	IO218NDB3
J6	IO216PDB3
J7	IO216NDB3
J8	VCCIB3
J9	GND
J10	VCC
J11	VCC
J12	VCC
J13	VCC
J14	GND
J15	VCCIB1
J16	IO83NPB1
J17	IO86NPB1
J18	IO90PPB1
J19	IO87NDB1
J20	NC
J21	IO89PDB1
J22	IO89NDB1
K1	IO211PDB3
K2	IO211NDB3
K3	NC
K4	IO210PPB3
K5	IO213NDB3
K6	IO213PDB3
K7	GFC1/IO209PPB3
K8	VCCIB3
K9	VCC
K10	GND
K11	GND
K12	GND
K13	GND
K14	VCC
K15	VCCIB1
K16	GCC1/IO91PPB1
K17	IO90NPB1
K18	IO88PDB1

Revision	Changes	Page
Revision 10 (continued)	"TBD" for 3.3 V LVCMOS Wide Range in Table 2-28 • I/O Output Buffer Maximum Resistances1 through Table 2-30 • I/O Output Buffer Maximum Resistances1 was replaced by "Same as regular 3.3 V" (SAR 33852).	2-26 to 2-28
	The equations in the notes for Table 2-31 • I/O Weak Pull-Up/Pull-Down Resistances were corrected (SAR 32470).	2-28
	"TBD" for 3.3 V LVCMOS Wide Range in Table 2-32 • I/O Short Currents IOSH/IOSL through Table 2-34 • I/O Short Currents IOSH/IOSL was replaced by "Same as regular 3.3 V LVCMOS" (SAR 33852).	2-29 to 2-31
	In the "3.3 V LVCMOS Wide Range" section, values were added to Table 2-47 through Table 2-49 for IOSL and IOSH, replacing "TBD" (SAR 33852).	2-39 to 2-40
	The following sentence was deleted from the "2.5 V LVCMOS" section (SAR 24916): "It uses a 5 V–tolerant input buffer and push-pull output buffer."	2-47
	The table notes were revised for Table 2-90 • LVDS Minimum and Maximum DC Input and Output Levels (SAR 33859).	2-66
	Values were added for $F_{DDRIMAX}$ and F_{DDOMAX} in Table 2-102 • Input DDR Propagation Delays and Table 2-104 • Output DDR Propagation Delays (SAR 23919).	2-78, 2-80
	Table 2-115 • ProASIC3 CCC/PLL Specification was updated. A note was added to indicate that when the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available (SAR 25705).	2-90
	The following figures were deleted (SAR 29991). Reference was made to a new application note, *Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs*, which covers these cases in detail (SAR 21770). Figure 2-34 • Write Access after Write onto Same Address Figure 2-35 • Read Access after Write onto Same Address Figure 2-35 • Read Access after Write onto Same Address The port names in the SRAM "Timing Waveforms", SRAM "Timing Characteristics" tables, Figure 2-39 • FIFO Reset, and the FIFO "Timing Characteristics" tables were revised to ensure consistency with the software names (SARs 29991, 30510).	2-92, 2-94, 2-99 2-102
	The "Pin Descriptions" chapter has been added (SAR 21642).	3-1
	Package names used in the "Package Pin Assignments" section were revised to match standards given in *Package Mechanical Drawings* (SAR 27395).	4-1
July 2010	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The "ProASIC3 Device Status" table on page IV indicates the status for each device in the device family.	N/A